

10/560234

**PATENT APPLICATION**

IAP13 Rec'd PCT/PTO 12 DEC 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

TARRANT et al

International Appln. No.: PCT/GB2004/002417

Filed: Concurrently herewith

Attorney Dkt. No.: 59553.00019

For: METHOD OF MANUFACTURING DOPED SEMICONDUCTING MATERIALS

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

**Attention: PCT DO/EO/US**

December 12, 2005

Sir:

This is an Information Disclosure Statement submitted under 37 C.F.R.1.97(b).

The references cited in the attached Form PTO-1449 were cited in the enclosed International Search Report issued by the European Patent Office in connection with the above international application. It is understood that the European Patent Office has sent a copy of each of the cited references to the U.S. Patent and Trademark Office. However, for the Examiner's convenience, the cited references are attached hereto.

In view of the above, all requirements of 37 CFR 1.97 and all official guidelines pertaining to Information Disclosure Statements have been complied with, and it is

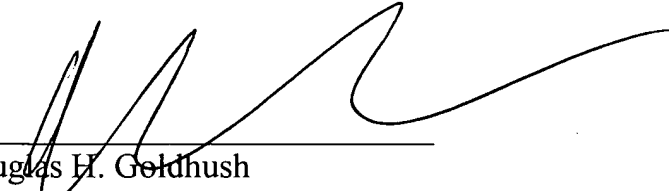
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therefore respectfully requested that the Examiner consider the references and make them of record in this application.

In the event that there are any fees due with respect to the filing of this paper, please charge Counsel's Deposit Account No. 50-2222.

Respectfully submitted,

  
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Enclosures: PTO-1449 Form  
International Search Report  
7 References

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 59553.00019	<div style="font-size: 2em; font-weight: bold;">10/260284</div> SERIAL NO. New Application
LIST OF REFERENCES CITED BY APPLICANT  <i>(Use several sheets if necessary)</i>		APPLICANT TARRANT et al	
		FILING DATE December 12, 2005	GROUP Not yet assigned

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
	AA						
	AB						

**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB-CLASS	<u>TRANSLATION</u>		
							YES	NO	PART.
	AC	0 890 661 A1	01/13/99	European			xx		
	AD								
	AE								

**OTHER REFERENCES** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

	AF	Weinstein et al, "A class of chemical pinning centers including two elements foreign to HTS" Physica C, Vol. 383, no. 4, January 1, 2003, pages 438-444, XP004399226.
	AG	Weinstein et al, "Very High values of Jc obtained in NdBa2Cu30x by use of the U/n process" Physica C., vol. 383, no. 3, December 15, 2002, pages 214-222, XP004391510.
	AH	Babu et al, "Effect of the addition of depleted UO2 on the microstructure of melt processed Y-Ba-Cu-O superconductors" Physica C., Vol. 372-376, August 2002, pages 1183-1186, Xp004375638.
	AI	Weinstein et al, "The role of uranium, with and without irradiation, in the achievement of Jc {300,000 A cm<-2> at 77 K in large grain melt-textured Y123", Materials Science and Engineering B, ElSevier Sequoia, vol. 53, no. 1-2, May 1, 1998, pages 38-44, XP004139989.
	AJ	Sawh R-P et al, "Uranium chemistry and pinning centers in high temperature superconductor", Physica C., vol. 305, no. 3-4, September 1, 1998 pages 159-166, XP004150793.
	AK	Weinstein et al, "Properties of HTS for Successful U/n Processing", Physica C, vol. 341-348, November 2000, pages 1415-1418, XP004315950.

EXAMINER	DATE CONSIDERED
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.